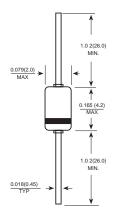




# HIGH SPEED SWITCHING DIODE

Reverse Voltage - 100 Volts Forward Current - 0.15 Ampere

# DO-35(GLASS)



Dimensions in inches and (millimeters)

## **FEATURES**

- Silicon epitaxial planar diode
- Switching diodes
- ◆ 500mw power dissipation
- High temperature soldering guaranteed 250°C/10 seconds,0.375" (9.5mm) lead length, 5 lbs. (2.3kg) tension

## **MECHANICAL DATA**

Case: DO-35 glass sealed envelope.

Terminals: Plated axial leads, solderable per MIL-STD-750,

Method 2026

Polarity: Color band denotes cathode end

**Mounting Position**: Any

Weight: 0.005 ounce, 0.14 grams(DO-35)

#### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified. Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

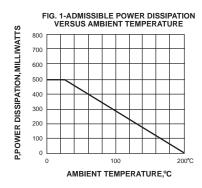
	SYMBOLS	1N4148	UNITS
Maximum repetitive peak reverse voltage	Vrrm	100	VOLTS
Maximum RMS voltage	VRMS	75	VOLTS
Maximum average forward rectified current 0.375"(9.5mm) lead length at Ta=25°C	l(AV)	150	mAmps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	lfsm	500	mAmps
Maximum instantaneous forward voltage at 10mA	VF	1.0	Volts
Maximum DC reverse current Ta=25°C VR=75V at rated DC blocking voltage Ta=100°C VR=20V	lR	5.0 50	μА
Maximum reverse recovery time (NOTE 1)	trr	4.0	ns
Typical junction capacitance (NOTE 2)	Сл	4.0	pF
Operating junction and storage temperature range	ТЈ,Тѕтс	-65 to +200	°C

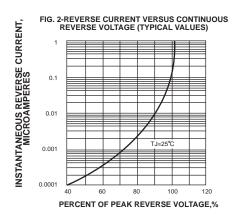
### NOTES:

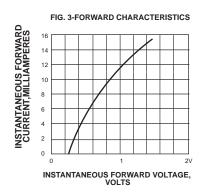
Rev.: 1-Dec-2015

- 1.Test condition:IF=10mA,IR=10mA,Irr=1mA,VR=6V,RL=100 $\Omega$ .
- 2.Measured at 1.0 MHz and applied reverse voltage of 4.0 volts

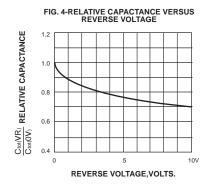
# **RATINGS AND CHARACTERISTIC CURVES 1N4148**



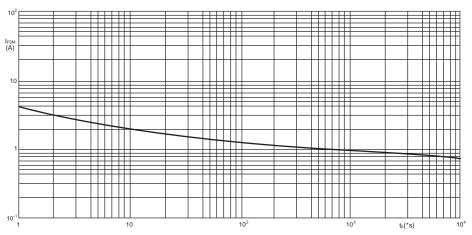




Rev.: 1-Dec-2015







Based on square wave currents. T<sub>i=25\*</sub> prior to surge.